

ABSTRACT OF THE DISCLOSURE

Power semiconductor switching devices, power converters, integrated circuit assemblies, integrated circuitry, power current switching methods, methods of forming a power semiconductor switching device, power conversion methods, power semiconductor switching device packaging methods, and methods of forming a power transistor are described. One exemplary aspect provides integrated circuitry including a monolithic semiconductive substrate; a power semiconductor switching device comprising a plurality of field effect transistors formed using the monolithic semiconductive substrate and having a plurality of electrical contacts including a plurality of gate contacts, a plurality of source contacts coupled in parallel and a plurality of drain contacts coupled in parallel; and auxiliary circuitry formed using the monolithic semiconductive substrate and configured to couple with at least one of the electrical contacts of the power field effect transistors

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